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NTE56068 & NTE56069 TRIAC, 16A, High Commutation

Description:

The NTE56068 and NTE56069 are glass passivated, high commutation TRIACs in an isolated full-pack type package designed for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commute the full rated RMS current at the maximum rated junction temperature, without the aid of a snubber.

Absolute Maximum Ratings:

Repetitive Peak Off-State Voltage (Note 1), V_{DRM}	
NTE56068	600V
NTE56069	800V
RMS On-State Current (Full Sine Wave, $T_{HS} \leq 38^{\circ}C$), $I_T(RMS)$	16A
Non-Repetitive Peak On-State Current, I_{TSM}	
(Full Sine Wave, $T_J = +25^{\circ}C$ prior to Surge)	
$t = 20ms$	140A
$t = 16.7ms$	150A
I^2t for Fusing ($t = 10ms$), I^2t	$98A^2sec$
Repetitive Rate-of-Rise of On-State Current after Triggering, dI_T/dt	
($I_{TM} = 20A$, $I_G = 0.2A$, $dI_G/dt = 0.2A/\mu s$)	$100A/\mu s$
Peak Gate Current, I_{GM}	2A
Peak Gate Voltage, V_{GM}	5V
Peak Gate Power, P_{GM}	5W
Average Gate Power (Over Any 20ms Period), $P_{G(AV)}$	500mW
Operating Junction Temperature, T_J	$+125^{\circ}C$
Storage Temperature Range, T_{stg}	-40° to $+150^{\circ}C$
Thermal Resistance, Junction-to-Heatsink (Full or Half Cycle), R_{thJHS}	
With Heatsink Compound	4.0K/W
Without Heatsink Compound	5.5K/W
Typical Thermal Resistance, Junction-to-Ambient, R_{thJA}	55K/W

Note 1. Although not recommended, off-state voltages up to 800V may be applied without damage, but the TRIAC may switch to the on-state. The rate-of-rise of current should not exceed $15A/\mu s$.

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Gate Trigger Current MT ₂ (+), G (+)	I _{GT}	V _D = 12V, I _T = 0.1A, Note 2	2	18	50	mA
MT ₂ (+), G (-)			2	21	50	mA
MT ₂ (-), G (-)			2	34	50	mA
Latching Current MT ₂ (+), G (+)	I _L	V _D = 12V, I _T = 0.1A	-	31	60	mA
MT ₂ (+), G (-)			-	34	90	mA
MT ₂ (-), G (-)			-	30	60	mA
Holding Current	I _H	V _D = 12V, I _T = 0.1A	-	31	60	mA
On-State Voltage	V _T	I _T = 20A	-	1.2	1.5	V
Gate Trigger Voltage	V _{GT}	V _D = 12V, I _T = 0.1A	-	0.7	1.5	V
		V _D = 400V, I _T = 0.1A, T _J = +125°C	0.25	0.4	-	V
Off-State Leakage Current	I _D	V _D = V _{DRMmax} , T _J = +125°C	-	0.1	0.5	mA
Dynamic Characteristics						
Critical Rate-of-Rise of Off-State Voltage	dV _D /dt	V _{DM} = 67% V _{DRMmax} , T _J = +125°C, Exponential Waveform, Gate Open	1000	4000	-	V/μs
Critical Rate-of-Change of Commutating Current	di _{com} /dt	V _{DM} = 400V, T _J = +125°C, I _T RMS = 16A, without Snubber, Gate Open	-	28	-	A/ms
Gate Controlled Turn-On Time	t _{gt}	I _{TM} = 20A, V _D = V _{DRMmax} , I _G = 0.1A, di _G /dt = 5A/μs	-	2	-	μs
Isolation Characteristics						
RMS Isolation Voltage from All 3 Pins to External Heatsink	V _{ISOL}	f = 50 – 60Hz, Sinusoidal Waveform, R.H. ≤ 65%, Clean and Dustfree	-	-	2500	V
Capacitance from T2 to External Heatsink	C _{ISOL}	f = 1MHz	-	10	-	pF

Note 2. Device does not trigger in the MT₂ (-), G (+) quadrant.

